

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (ORIGINAL) A method for producing a Group III nitride crystal comprising:
growing a crystal in a nitrogen-containing atmosphere by reacting at least one Group III element selected from Ga, Al, and In with nitrogen in a melt that includes a flux including an alkali metal,
wherein the flux further includes Mg.
2. (ORIGINAL) The method according to claim 1, wherein Mg of the flux functions as at least one of a flux component and a doping component.
3. (CURRENTLY AMENDED) The method according to claim 1, wherein the flux includes as a doping component at least one selected from an alkaline-earth metal (~~other than Mg~~) and Zn ~~in addition to or instead of Mg~~.
4. (ORIGINAL) The method according to claim 1, wherein the nitrogen is supplied as a nitrogen-containing gas.
5. (ORIGINAL) The method according to claim 3, wherein the alkaline-earth metal is at least one selected from Ca, Be, Sr, and Ba.
6. (ORIGINAL) The method according to claim 1, wherein the flux is a mixed flux of Na and Mg.
7. (ORIGINAL) The method according to claim 6, wherein a proportion of Mg in the mixed flux is 0.001 to 10 mol%.

8. (ORIGINAL) The method according to claim 6, wherein the Group III element is Ga and the Group III nitride is GaN.
9. (ORIGINAL) A Group III nitride crystal produced by the method according to claim 1.
10. (ORIGINAL) The Group III nitride crystal according to claim 9, wherein a doping amount of Mg is more than 0 and not more than $1 \times 10^{20} \text{ cm}^{-3}$.
11. (CURRENTLY AMENDED) The Group III nitride crystal according to claim 9, wherein the Group III nitride crystal includes at least one selected from an alkaline-earth metal and Zn, and a total doping amount of Mg, the alkaline-earth metal (other than Mg), and Zn is more than 0 and not more than $1 \times 10^{17} \text{ cm}^{-3}$.
12. (ORIGINAL) The Group III nitride crystal according to claim 9, wherein an oxygen concentration of the crystal is 0 to $1 \times 10^{17} \text{ cm}^{-3}$.
13. (ORIGINAL) The Group III nitride crystal according to claim 9, wherein a resistivity (specific resistance) is not less than $1 \times 10^3 \Omega \cdot \text{cm}$.
14. (ORIGINAL) The Group III nitride crystal according to claim 9, wherein a resistivity (specific resistance) is not less than $1 \times 10^5 \Omega \cdot \text{cm}$.
15. (ORIGINAL) A Group III nitride substrate comprising the Group III nitride crystal according to claim 9.
16. (ORIGINAL) The Group III nitride substrate according to claim 15, wherein the substrate is a p-type substrate or a semi-insulating substrate.
17. (ORIGINAL) A field-effect transistor comprising the Group III nitride substrate according to claim 16.